

Weifeng Sun

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148
papers

911
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g-index

166
ext. papers

1,261
ext. citations

3.4
avg, IF

4.54
L-index

#	Paper	IF	Citations
148	Repetitive Unclamped-Inductive-Switching-Induced Electrical Parameters Degradations and Simulation Optimizations for 4H-SiC MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4331-4338	3.9	40
147	Further Study of the U-Shaped Channel SOI-LIGBT With Enhanced Current Density for High-Voltage Monolithic ICs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1161-1167	2.9	30
146	Electrical Characteristic Study of an SOI-LIGBT With Segmented Trenches in the Anode Region. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2003-2008	2.9	28
145	Investigations on the Degradations of Double-Trench SiC Power MOSFETs Under Repetitive Avalanche Stress. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 546-552	2.9	28
144	Fast Computation of Radial Vibration in Switched Reluctance Motors. <i>IEEE Transactions on Industrial Electronics</i> , 2018 , 65, 4588-4598	8.9	26
143	Comprehensive Investigations on Degradations of Dynamic Characteristics for SiC Power MOSFETs Under Repetitive Avalanche Shocks. <i>IEEE Transactions on Power Electronics</i> , 2019 , 34, 2748-2757	7.2	23
142	Repetitive-Avalanche-Induced Electrical Parameters Shift for 4H-SiC Junction Barrier Schottky Diode. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 601-605	2.9	20
141	A Novel Silicon-on-Insulator Lateral Insulated-Gate Bipolar Transistor With Dual Trenches for Three-Phase Single Chip Inverter ICs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 693-695	4.4	20
140	A Low-Cost Constant Current Control Method for DCM and CCM in Digitally Controlled Primary-Side Regulation Flyback Converter. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2018 , 6, 1483-1494	5.6	19
139	Comprehensive Analysis of Electrical Parameters Degradations for SiC Power MOSFETs Under Repetitive Short-Circuit Stress. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5440-5447	2.9	19
138	High voltage thick SOI-LIGBT with high current density and latch-up immunity 2015 ,		17
137	A Novel Charge-Imbalance Termination for Trench Superjunction VDMOS. <i>IEEE Electron Device Letters</i> , 2010 , 31, 1434-1436	4.4	17
136	Novel Digital Control Method for Improving Dynamic Responses of Multimode Primary-Side Regulation Flyback Converter. <i>IEEE Transactions on Power Electronics</i> , 2017 , 32, 1457-1468	7.2	16
135	A Review on Hot-Carrier-Induced Degradation of Lateral DMOS Transistor. <i>IEEE Transactions on Device and Materials Reliability</i> , 2018 , 18, 298-312	1.6	16
134	A high current density SOI-LIGBT with Segmented Trenches in the Anode region for suppressing negative differential resistance regime 2015 ,		15
133	High precision constant voltage digital control scheme for primary-side controlled flyback converter. <i>IET Power Electronics</i> , 2016 , 9, 2522-2533	2.2	15
132	Novel Snapback-Free Reverse-Conducting SOI-LIGBT With Dual Embedded Diodes. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 1187-1192	2.9	13

131	Hot-Carrier-Induced Degradations and Optimizations for Lateral DMOS Transistor With Multiple Floating Poly-Gate Field Plates. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3275-3281	2.9	12
130	Digital regulation scheme for multimode primary-side controlled flyback converter. <i>IET Power Electronics</i> , 2016 , 9, 782-788	2.2	12
129	A digital detecting method for synchronous rectification based on dual-verification for LLC resonant converter 2018 ,		11
128	Low-Loss SOI-LIGBT With Dual Deep-Oxide Trenches. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3282-3286	2.9	10
127	Interfacial damage extraction method for SiC power MOSFETs based on C-V characteristics 2017 ,		10
126	Low-Loss SOI-LIGBT With Triple Deep-Oxide Trenches. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3756-3761	2.9	10
125	Hot-Carrier-Induced On-Resistance Degradation of n-Type Lateral DMOS Transistor With Shallow Trench Isolation for High-Side Application. <i>IEEE Transactions on Device and Materials Reliability</i> , 2015 , 15, 458-460	1.6	10
124	Resonance Reduction by Optimal Switch Angle Selection in Switched Reluctance Motor. <i>IEEE Transactions on Industrial Electronics</i> , 2020 , 67, 1867-1877	8.9	10
123	A Two-Stage BuckBoost Integrated LLC Converter With Extended ZVS Range and Reduced Conduction Loss for High-Frequency and High-Efficiency Applications. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 727-743	5.6	10
122	A U-Shaped Channel SOI-LIGBT With Dual Trenches. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 2587-2591	2.5	9
121	An Integrated Bootstrap Diode Emulator for 600-V High Voltage Gate Drive IC With P-Sub/P-Epi Technology. <i>IEEE Transactions on Power Electronics</i> , 2016 , 31, 518-523	7.2	9
120	Investigation on degradation mechanism and optimization for SiC power MOSFETs under long-term short-circuit stress 2018 ,		9
119	Off-State Stress Degradation Analysis and Optimization for the High-Voltage SOI-pLED MOS With Thick Gate Oxide. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 3632-3638	2.9	9
118	TC-LIGBTs on the Thin Sol Layer for the High Voltage Monolithic ICs With High Current Density and Latch-Up Immunity. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 3814-3820	2.9	9
117	Electrical Characteristic Investigation on a Novel Double-Well Isolation Structure in 600-V-Class High-Voltage Integrated Circuits. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 3477-3481	2.9	9
116	Comparisons of hot-carrier degradation behavior in SOI-LIGBT and SOI-LDMOS with different stress conditions. <i>Solid-State Electronics</i> , 2010 , 54, 1598-1601	1.7	9
115	Turn-Off Transient of Superjunction SOI Lateral IGBTs: Mechanism and Optimization Strategy. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1409-1415	2.9	9
114	A Single-Switched High-Switching-Frequency Quasi-Resonant Flyback Converter. <i>IEEE Transactions on Power Electronics</i> , 2019 , 34, 8775-8786	7.2	9

113	Influence of switch angles on second-order current harmonic and resonance in switched reluctance motors. <i>IET Electric Power Applications</i> , 2018 , 12, 1247-1255	1.8	9
112	Single Pulse Unclamped-Inductive-Switching Induced Failure and Analysis for 650 V p-GaN HEMT. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 11328-11331	7.2	8
111	A Phase-Shift Triple Full-Bridge Converter With Three Shared Leading Legs. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2018 , 6, 1912-1920	5.6	8
110	Noise Immunity and its Temperature Characteristics Study of the Capacitive-Loaded Level Shift Circuit for High Voltage Gate Drive IC. <i>IEEE Transactions on Industrial Electronics</i> , 2018 , 65, 3027-3034	8.9	8
109	Electrical Parameters Degradations and Optimizations of SOI-LIGBT Under Repetitive Unclamped-Inductive-Switching Conditions. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1644-1649	2.9	8
108	A Robust W-Shape-Buffer LIGBT Device With Large Current Capability. <i>IEEE Transactions on Power Electronics</i> , 2014 , 29, 4466-4469	7.2	8
107	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2014 , 14, 523-528	1.6	8
106	Investigation on Self-Adjust Conductivity Modulation SOI-LIGBT Structure (SCM-LIGBT) for Monolithic High-Voltage IC. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3762-3767	2.9	8
105	. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 1158-1163	2.9	8
104	A Digital Control Scheme for PSR Flyback Converter in CCM and DCM. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2020 , 8, 2837-2849	5.6	8
103	A Novel Lateral DMOS Transistor With H-Shape Shallow-Trench-Isolation Structure. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5218-5221	2.9	8
102	Implementation of a High-Precision and Wide-Range Time-to-Digital Converter With Three-Level Conversion Scheme. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2017 , 64, 181-185	3.5	7
101	A new high-voltage interconnection shielding method for SOI monolithic ICs. <i>Solid-State Electronics</i> , 2017 , 133, 25-30	1.7	7
100	A High-Frequency Model for a PCM Buck Converter. <i>IEEE Transactions on Power Electronics</i> , 2015 , 30, 2304-2312	7.2	7
99	High-temperature electrical performances and physics-based analysis of p-GaN HEMT device. <i>IET Power Electronics</i> , 2020 , 13, 420-425	2.2	7
98	Understanding Short-Circuit Failure Mechanism of Double-Trench SiC Power MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5593-5599	2.9	7
97	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1430-1434	2.9	7
96	Comparison Investigations on Unclamped-Inductive-Switching Behaviors of Power GaN Switching Devices. <i>IEEE Transactions on Industrial Electronics</i> , 2021 , 1-1	8.9	7

95	Mechanism and Novel Structure for di/dt Controllability in U-Shaped Channel Silicon-on-Insulator Lateral IGBTs. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1658-1661	4.4	6
94	A capacitive-loaded level shift circuit for improving the noise immunity of high voltage gate drive IC 2015 ,		6
93	Sampled-Data Modeling for PCM and ZVS Controlled Critical Conduction Mode (CrCM) Active Clamp Flyback (ACF) Converter at Variable Switching Frequency. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2020 , 67, 3588-3600	3.9	6
92	Lateral DMOS With Partial-Resist-Implanted Drift Region for Alleviating Hot-Carrier Effect. <i>IEEE Transactions on Device and Materials Reliability</i> , 2017 , 17, 780-784	1.6	6
91	Optimization of V_{CE} Plateau for Deep-Oxide Trench SOI Lateral IGBT During Inductive Load Turn-OFF. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3862-3868	2.9	6
90	Turn-off failure in multi-finger SOI-LIGBT used for single chip inverter ICs. <i>Solid-State Electronics</i> , 2017 , 137, 29-37	1.7	6
89	Anomalous output characteristic shift for the n-type lateral diffused metal-oxide-semiconductor transistor with floating P-top layer. <i>Applied Physics Letters</i> , 2014 , 104, 153512	3.4	6
88	An accurate design method of RCD circuit for flyback converter considering diode reverse recovery 2016 ,		6
87	Comprehensive Investigation on Electrical Properties of nLDMOS and pLDMOS Under Mechanical Strain. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1012-1017	2.9	6
86	Comparison of short-circuit characteristics of trench gate and planar gate U-shaped channel SOI-LIGBTs. <i>Solid-State Electronics</i> , 2017 , 135, 24-30	1.7	5
85	Hot-Carrier-Induced Degradations Investigations for 600 V SOI-LIGBT by an Improved Charge Pumping Solution. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 634-637	2.9	5
84	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3492-3495	2.9	5
83	Verification of Single-Pulse Avalanche Failure Mechanism for Double-Trench SiC Power MOSFETs. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 2190-2200	5.6	5
82	Investigation on the Degradation Mechanism for SiC Power MOSFETs Under Repetitive Switching Stress. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 2180-2189	5.6	5
81	Experimental Investigation on the Electrical Properties of Lateral IGBT Under Mechanical Strain. <i>IEEE Electron Device Letters</i> , 2019 , 40, 937-940	4.4	4
80	Super Field Plate Technique That Can Provide Charge Balance Effect for Lateral Power Devices Without Occupying Drift Region. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 2218-2222	2.9	4
79	Modeling Avalanche Induced Degradation for 4H-SiC Power MOSFETs. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 11299-11303	7.2	4
78	A simple average current control with time-length equality for primary-side regulation flyback converter with constant output current control. <i>International Journal of Circuit Theory and Applications</i> , 2018 , 46, 2477-2494	2	4

77	A novel digital multi-mode control strategy with PSM for primary-side flyback converter. <i>International Journal of Electronics</i> , 2017 , 104, 840-854	1.2	4
76	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2017 , 17, 450-457	1.6	4
75	Analysis of a Time-Length Compensation Algorithm for Elimination of Subharmonic Oscillation and Application in a Digitally Controlled Primary-Side Regulation Flyback Converter. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2017 , 5, 1710-1719	5.6	4
74	Zero-steady-state-error compensation method in application of peak current mode buck converter with fast transient response. <i>IET Power Electronics</i> , 2015 , 8, 647-655	2.2	4
73	. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3767-3773	2.9	4
72	A noise immunity improved level shift structure for a 600 V HVIC. <i>Journal of Semiconductors</i> , 2013 , 34, 065008	2.3	4
71	Single-Pulse Avalanche Failure Investigations of Si-SJ-mosfet and SiC-mosfet by Step-Control Infrared Thermography Method. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 5180-5189	7.2	4
70	Investigation on Hot-Carrier-Induced degradation of STI-nLDMOS with two-step-oxide process for high side application 2016 ,		4
69	Investigations on Electrical Parameters Degradations of p-GaN HEMTs Under Repetitive UIS Stresses. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 2227-2234	5.6	4
68	Small Signal Modeling and Control Loop Design of Critical Conduction Mode Active Clamp Flyback Converter. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 7250-7263	7.2	4
67	A Novel Digital Control Method of Primary-Side Regulated Flyback With Active Clamping Technique. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2021 , 68, 950-962	3.9	4
66	Extraction method of interfacial injected charges for SiC power MOSFETs. <i>Superlattices and Microstructures</i> , 2018 , 113, 706-712	2.8	4
65	. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 10827-10841	7.2	4
64	New Digital Control Method for Improving Dynamic Response of Synchronous Rectified PSR Flyback Converter With CCM and DCM Modes. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 12347-12358	7.2	3
63	U-shaped channel SOI-LIGBT with dual trenches to improve the trade-off between saturation voltage and turn-off loss 2017 ,		3
62	Mobility Fluctuation-Induced Low-Frequency Noise in Ultrascaled Ge Nanowire nMOSFETs With Near-Ballistic Transport. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2573-2577	2.9	3
61	Comprehensive investigation on mechanical strain induced performance boosts in LDMOS 2018 ,		3
60	Integrated GaN MIS-HEMT with Multi-Channel Heterojunction SBD Structures 2019 ,		3

59	Reliability concern and design for the lateral insulator gate bipolar transistor based on SOI substrate. <i>Solid-State Electronics</i> , 2013 , 85, 28-35	1.7	3
58	Fast recovery SOI PiN diode with multiple trenches. <i>Superlattices and Microstructures</i> , 2017 , 111, 405-413.	3.8	3
57	Breakdown Voltage Walk-in Phenomenon and Optimization for the Trench-Gate p-Type VDMOS Under Single Avalanche Stress. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 2445-2450	2.9	3
56	Electrical performances degradations and physics based mechanisms under negative bias temperature instability stress for p-GaN gate high electron mobility transistors. <i>Semiconductor Science and Technology</i> , 2021 , 36, 014007	1.8	3
55	Simulation Study of A 1200V 4H-SiC Lateral MOSFET With Reduced Saturation Current. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	3
54	Silicon-on-Insulator Lateral DMOS With Potential Modulation Plates and Multiple Deep-Oxide Trenches. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 5073-5077	2.9	3
53	Performance Boosts in n-Type Lateral Double-Diffused MOSFET With Process-Induced Strain Using Contact Etch Stop Layer Stressor. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 421-424	2.9	3
52	A LLC resonant converter with dual resonant frequency for high light load efficiency. <i>International Journal of Electronics</i> , 2017 , 1-15	1.2	2
51	Hot-Carrier-Induced Degradation and Optimization for Lateral DMOS With Split-STI-Structure in the Drift Region. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 2869-2875	2.9	2
50	A Wide Dynamic Range and Low Bit Error Pixel TDC Suitable for Array Application. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2019 , 66, 1805-1809	3.5	2
49	Hot-Carrier-Induced Degradation and Optimization for 700-V High-Voltage Lateral DMOS by the AC Stress. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 1090-1097	2.9	2
48	An Integrated Bias Voltage Control Method for SPAD Arrays. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 1723-1726	2.2	2
47	Switch-OFF Avalanche-Breakdown-Induced Electrical Degradations of RF-LDMOS Transistor for SMPAs Applications. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4719-4723	2.9	2
46	Study on EMI Characteristics of the Superjunction DMOS in Flyback Converter System. <i>IEEE Transactions on Device and Materials Reliability</i> , 2017 , 17, 692-697	1.6	2
45	Hot-carrier degradation mechanism for p-type symmetric LDMOS transistor with thick gate oxide. <i>Electronics Letters</i> , 2012 , 48, 1545-1546	1.1	2
44	Reliability Concerns on LDMOS With Different Split-STI Layout Patterns. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 185-192	2.9	2
43	A New Modulation Strategy for Four-switch Buck-boost Converter with Reduced Freewheeling Current 2020 ,		2
42	Complete Avalanche Process and Failure Mechanism of Trench-Gate FS-IGBT Under Unclamped Inductive Switching by Using Infrared Visualization Method. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3908-3911	2.9	2

41	Study and Implementation of 600-V High-Voltage Gate Driver IC With the Common-Mode Dual-Interlock Technique for GaN Devices. <i>IEEE Transactions on Industrial Electronics</i> , 2021 , 68, 1506-1514	8.9	2
40	Influence of Latch-Up Immunity Structure on ESD Robustness of SOI-LIGBT Used As Output Device. <i>IEEE Transactions on Device and Materials Reliability</i> , 2018 , 18, 284-290	1.6	2
39	High-Voltage a-IGZO TFTs With the Stair Gate-Dielectric Structure. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 4462-4466	2.9	2
38	An Improved Adaptive Synchronous Rectification Method With the Enhanced Capacity to Eliminate Reverse Current. <i>IEEE Transactions on Power Electronics</i> , 2021 , 1-1	7.2	2
37	A time-length compensation algorithm for sub-harmonic oscillation elimination in digital controlled primary-side regulation flyback converter 2017 ,		1
36	Analog Compensator Design for Half Bridge LLC Resonant Converter 2019 ,		1
35	Reliability concern of quasi-vertical GaN Schottky barrier diode under high temperature reverse bias stress. <i>Superlattices and Microstructures</i> , 2019 , 130, 233-240	2.8	1
34	Duty-cycle-accelerated hot-carrier degradation and lifetime evaluation for 700V lateral DMOS 2018 ,		1
33	Comprehensive Investigation on Electrical Properties of Split-Gate Trench Power MOSFETs Under Mechanical Strains. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-5	2.9	1
32	Novel Multiple-Layer Stack Capacitor and Its Application in the IRPFA Readout Circuit. <i>IEEE Access</i> , 2021 , 9, 161806-161813	3.5	1
31	Small-signal modelling for time-length compensation algorithm in current controlled converters. <i>International Journal of Circuit Theory and Applications</i> , 2020 , 48, 148-155	2	1
30	A self-adaptive pulse generator to realize extremely low power consumption and high reliability of high voltage gate driver IC. <i>Analog Integrated Circuits and Signal Processing</i> , 2020 , 105, 13-20	1.2	1
29	Experimental Investigation on the Electrical Properties of SOI-LIGBT Under Total-Ionizing-Dose Radiation 2020 ,		1
28	Hot-Carrier-Induced Reliability Concerns for Lateral DMOS Transistors with Split-STI Structures 2021 ,		1
27	System Performance Optimization for Dual-Loop Dual-Variable Controlled Active Clamp Flyback Converter Using Decoupling Compensation Technique 2021 ,		1
26	High-Voltage Electron Injection Enhanced TC-LIGBT on 1.5- μm -Thin SOI Layer for Reducing the Forward Voltage Drop. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4873-4879	2.9	1
25	. <i>IEEE Journal of Emerging and Selected Topics in Power Electronics</i> , 2021 , 9, 3307-3321	5.6	1
24	Design and implementation of a hybrid DPWM under 50 ps resolution based on general-purpose FPGA. <i>International Journal of Circuit Theory and Applications</i> , 2021 , 49, 114-127	2	1

23	Lightning Surge Robustness Analysis and Optimization for an LED Driver Based on a Flyback Converter. <i>IEEE Transactions on Industrial Electronics</i> , 2021 , 68, 10449-10458	8.9	1
22	Experimental investigation on total-ionizing-dose radiation effects on the electrical properties of SOI-LIGBT. <i>Solid-State Electronics</i> , 2021 , 175, 107952	1.7	1
21	Comparative Study on Vibration Mode with Different Current Amplitudes and Modeling of Radial Vibration in Switched Reluctance Motor 2018 ,		1
20	Understanding Electrical Parameter Degradations of P-GaN HEMT Under Repetitive Short-Circuit Stresses. <i>IEEE Transactions on Power Electronics</i> , 2021 , 36, 12173-12176	7.2	1
19	A Silicon-On-Insulator Lateral IGBT With Segmented Trenches for Improving Short-Circuit Withstanding Capability. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-4	2.9	1
18	Investigation on the Degradation Mechanism for GaN Cascode Device Under Repetitive Hard-Switching Stress. <i>IEEE Transactions on Power Electronics</i> , 2021 , 1-1	7.2	0
17	. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 3483-3489	2.9	0
16	Numerical Study of Novel GaN HEMTs With Integrated SBDs for Ultrahigh Reverse Conduction Capability. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 931-933	2.9	0
15	Quasisaturation Effect and Optimization for 4H-SiC Trench MOSFET With P+ Shielding Region. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 4550-4556	2.9	0
14	Experimental Investigations on the Electrical Properties of 4H-SiC Power MOSFETs Under Biaxial and Uniaxial Mechanical Strains. <i>IEEE Transactions on Power Electronics</i> , 2022 , 37, 55-58	7.2	0
13	Numerical study of a novel GaN vertical FinFET with a β -base structure for high switching performance. <i>Journal of Computational Electronics</i> , 1	1.8	0
12	Unclamped-Inductive-Switching Behaviors of p-GaN HEMTs at Cryogenic Temperature. <i>IEEE Transactions on Power Electronics</i> , 2022 , 1-1	7.2	0
11	Failure Analysis and Improvement for High Power Single-Phase Module. <i>IEEE Transactions on Device and Materials Reliability</i> , 2017 , 17, 170-175	1.6	
10	Analysis and optimization of the switching noise for Super-junction MOSFET in full bridge converter system. <i>Solid-State Electronics</i> , 2019 , 161, 107638	1.7	
9	Endurance degradation and lifetime model of p-channel floating gate flash memory device with 2T structure. <i>Solid-State Electronics</i> , 2017 , 134, 58-64	1.7	
8	Hot-Carrier-Induced Reliability for Lateral DMOS Transistors With Split-STI Structures. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 9, 1188-1193	2.3	
7	Analysis of OFF-state dynamic avalanche instability in silicon-on-insulator lateral IGBTs at low temperature. <i>Microelectronics Reliability</i> , 2020 , 107, 113600	1.2	
6	Integrated 100 V bootstrap diode with enhanced reverse recovery characteristics for eGaN-field effect transistor gate drivers. <i>Electronics Letters</i> , 2020 , 56, 308-309	1.1	

- 5 Anomalous output characteristics shrinkage in STI-LDMOS transistor after repetitive I-V scanning measurements. *Superlattices and Microstructures*, **2019**, 128, 204-211 2.8
- 4 A 600V PiN diode with partial recessed anode and double-side Schottky engineering for fast reverse recovery. *Superlattices and Microstructures*, **2019**, 128, 56-66 2.8
- 3 Simulation Study of Novel Trench Gate U-Shaped Channel SOI Lateral IGBTs With Suppressed Gate Voltage Overshoot and Reduced di/dt. *IEEE Transactions on Electron Devices*, **2021**, 68, 3930-3935 2.9
- 2 Device and Circuit Design for Improving the Freewheeling Characteristics of High Voltage Monolithic Integrated Circuit. *IEEE Transactions on Industrial Electronics*, **2021**, 68, 11420-11427 8.9
- 1 An Ultraviolet Photon Counting Imaging System Based on a SiC SPAD Array. *IEEE Photonics Technology Letters*, **2021**, 33, 1213-1216 2.2